

214019US-2



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

16/B  
T. Steptoe  
5/20/03

IN RE APPLICATION OF:

EIJI SAKAGAMI

:EXAMINER: H. WEISS

SERIAL NO.: 09/955,076

:

FILED: SEPTEMBER 19, 2001

:GROUP ART UNIT: 2814

FOR: NONVOLATILE SEMICONDUCTOR MEMORY  
HAVING MONOS STRUCTURE AND METHOD ...

AMENDMENT UNDER 37 C.F.R. §1.114(c)

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated November 8, 2002 and Advisory Action dated March 5, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS

**Please amend Claim 1 to read as follows:<sup>1</sup>**

1. (Twice Amended) A nonvolatile semiconductor memory comprising:
  - a semiconductor substrate;
  - a first transistor formed on a surface of said semiconductor substrate and including a first gate insulating film and a first gate electrode;
  - a second transistor formed on the surface of said semiconductor substrate and including a second gate insulating film and a second gate electrode; and

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<sup>1</sup>The changes to Claim 1 are denoted using underscoring and bracketing in the marked-up copy herewith.